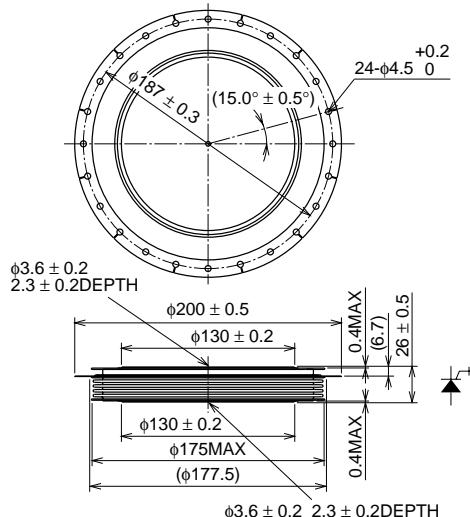


FGC6000AX-120DSHIGH POWER INVERTER USE
PRESS PACK TYPE**FGC6000AX-120DS**

- ITQRM Repetitive controllable on-state current 6000A
- IT(AV) Average on-state current 2000A
- VDRM Repetitive peak off-state voltage 6000V
- Anode short type

OUTLINE DRAWING

Dimensions in mm

**APPLICATION**

Inverters, DC choppers, Induction heaters, DC to DC converters.

MAXIMUM RATINGS

Symbol	Parameter	Voltage class	Unit
VRM	Repetitive peak reverse voltage	22	V
VRSM	Non-repetitive peak reverse voltage	22	V
VR(DC)	DC reverse voltage	22	V
VDRM	Repetitive peak off-state voltage*	6000	V
VDSM	Non-repetitive peak off-state voltage*	6000	V
VD(DC)	DC off-state voltage*	4800	V
VLTDS	Long term DC stability voltage*	3200	V

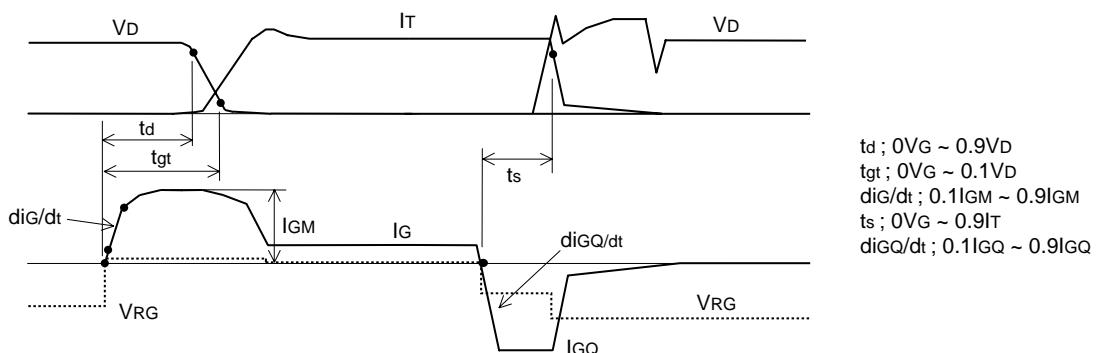
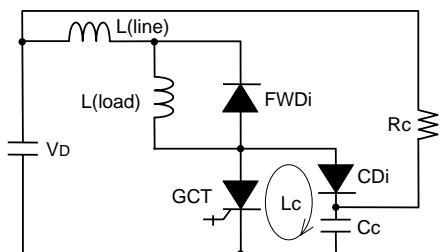
* : VGK = -2V

Symbol	Parameter	Conditions	Ratings	Unit
ITQRM	Repetitive controllable on-state current	VDM = 5500V, VD = 3000V, LC = 0.3μH, VRG = 20V dIG/dt = 10000A/μs, Tj = 25/125°C (see Fig. 1, 2)	6000	A
IT(RMS)	RMS on-state current	Applied for all conduction angles	3100	A
IT(AV)	Average on-state current	f = 60Hz, sinewave θ = 180°, Tf = 72°C	2000	A
ITSM	Surge on-state current	One half cycle at 60Hz, Tj = 125°C	40	kA
I ² t	Current-squared, time integration		6.7 × 10 ⁶	A ² s
di/dt	Critical rate of rise of on-state current	IT = 6000A, VD = 3000V, IGM= 300A, Tj= 125°C dIG/dt = 200A/μs (see Fig. 1, 2)	1000	A/μs
VFGM	Peak forward gate voltage		10	V
VRGM	Peak reverse gate voltage		22	V
IFGM	Peak forward gate current		1500	A
IRGM	Peak reverse gate current		6000	A
PFGM	Peak forward gate power dissipation		15	kW
PRGM	Peak reverse gate power dissipation		180	kW
PFG(AV)	Average forward gate power dissipation		300	W
PRG(AV)	Average reverse gate power dissipation		900	W
T _j	Junction temperature		-40 ~ +125	°C
T _{stg}	Storage temperature		-40 ~ +150	°C
—	Mounting force required	(Recommended value 108kN)	98 ~ 118	kN
—	Weight	Typical value	3700	g

Mar. 2001

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V _{TM}	On-state voltage	I _T = 6000A, T _j = 125°C	—	—	4.0	V
I _{RRM}	Repetitive peak reverse current	V _{RM} = 22V, T _j = 125°C	—	—	100	mA
I _{DRM}	Repetitive peak off-state current	V _D = 6000V, V _{GK} = -2V, T _j = 125°C	—	—	320	mA
I _{GRM}	Reverse gate current	V _{RM} = 22V, T _j = 125°C	—	—	100	mA
d _{v/dt}	Critical rate of rise of off-state voltage	V _D = 3000V, V _{GK} = -2V, T _j = 125°C (see Fig. 3)	3000	—	—	V/μs
t _{GT}	Turn-on time	V _D = 3000V, I _T = 6000A, I _{GM} = 300A, T _j = 125°C d _{i/dt} = 1000A/μs, d _{IG/dt} = 200A/μs (see Fig. 2)	—	—	5.0	μs
t _S	Storage time	I _T = 6000A, V _D = 3000V, d _{IGQ/dt} = 10000A/μs, T _j = 125°C, L _C = 0.3μH, V _{RG} = 20V (see Fig. 2)	—	—	3.0	μs
I _{GT}	Gate trigger current	DC METHOD : V _D = 24V, R _L = 0.1Ω, T _j = 25°C	—	—	8.0	A
V _{GT}	Gate trigger voltage		—	—	1.5	V
R _{th(j-f)}	Thermal resistance	Junction to fin	—	—	0.0044	°C/W

Fig. 1 Turn-on and Turn-off waveform**Fig. 2 Turn-on and Turn-off test circuit**
(With clamp circuit)**Fig. 3 dv/dt test waveform**